

Power Electronics

Project: Design of a Full-Wave Rectifier and Buck Converter

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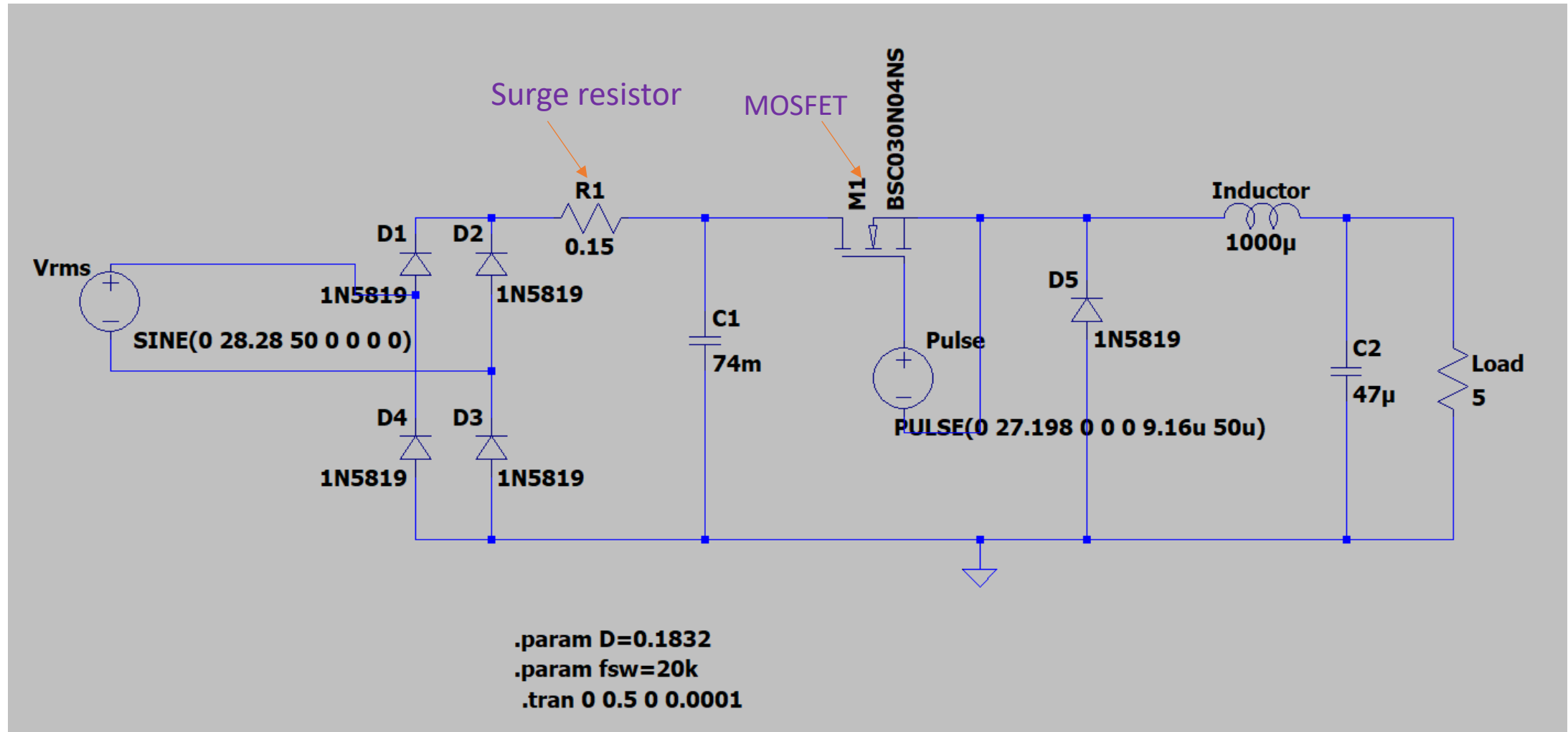
Course of Study:-Master in Commercial Vehicle Technology

Guided by:- M. Sc. Nielson Tschá

1. Introduction

- **Objective:**
- The goal of this project is to design a **power conversion system** consisting of a **single-phase full-wave rectifier** followed by a **buck converter** that meets specific ripple constraints under input voltage variations.

Schematic



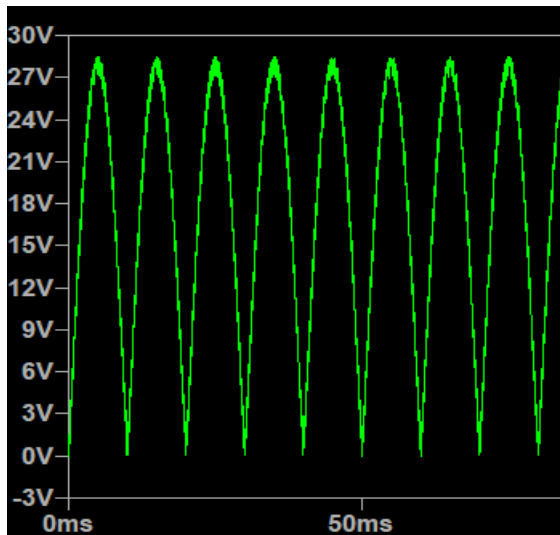
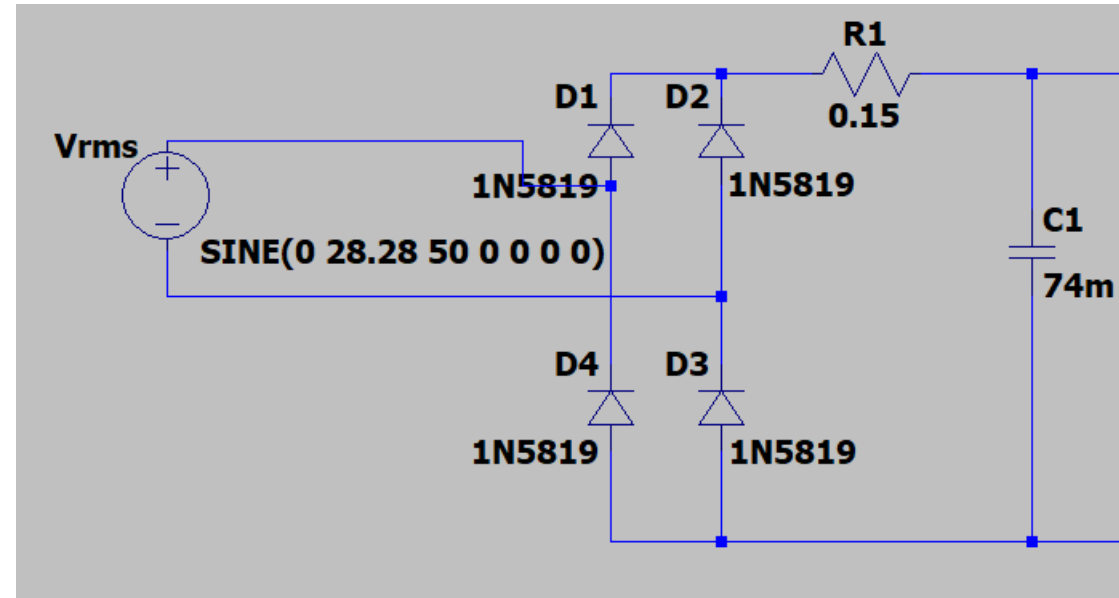
Design requirements

- Input Voltage = 20Vrms
- Switching frequency = 20kHz
- Output ripple current = 25%
- Output voltage ripple = 1.5%
- Load current = 1 Amp
- Output load = 5 ohm

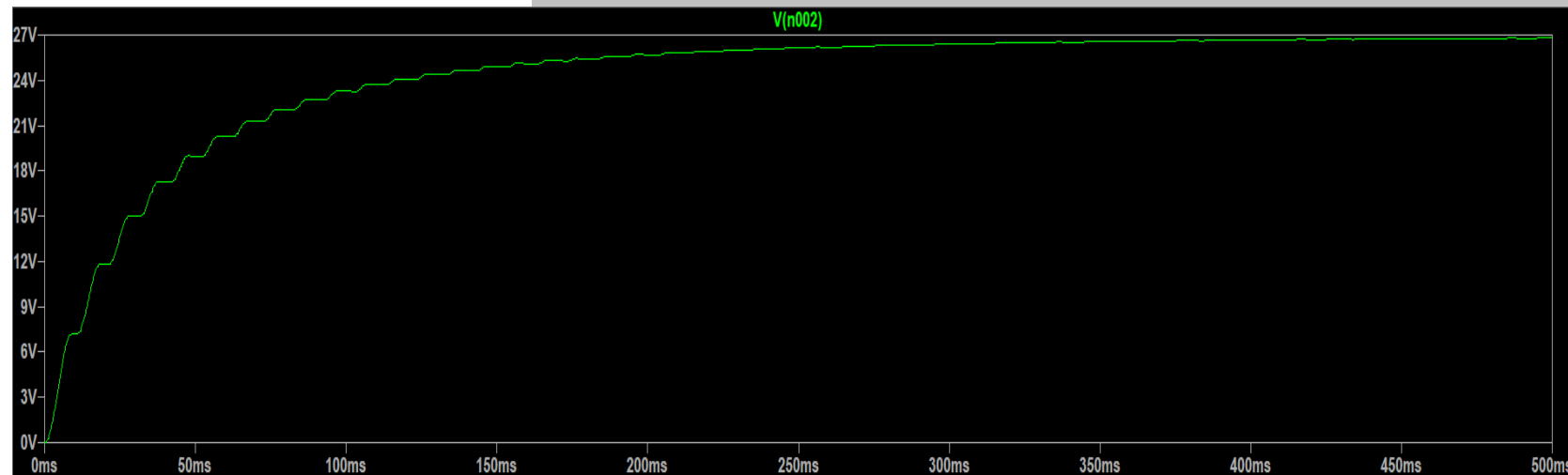
2. System Design

2.1 Rectifier stage

- Four 1N5819 Schottky diodes are arranged to rectify AC V_{rms} to DC supply.
- Resistor R1(0.15ohm) protects capacitor C1 from surge current
- Capacitor C1(74mf) stabilizes rectified voltage to constant 27.2v



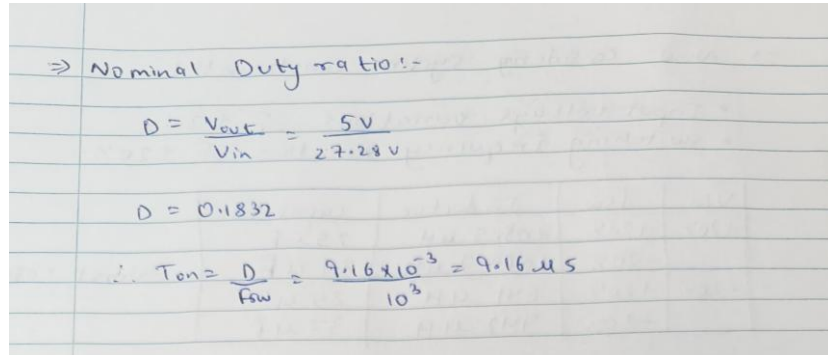
Without capacitor



With capacitor

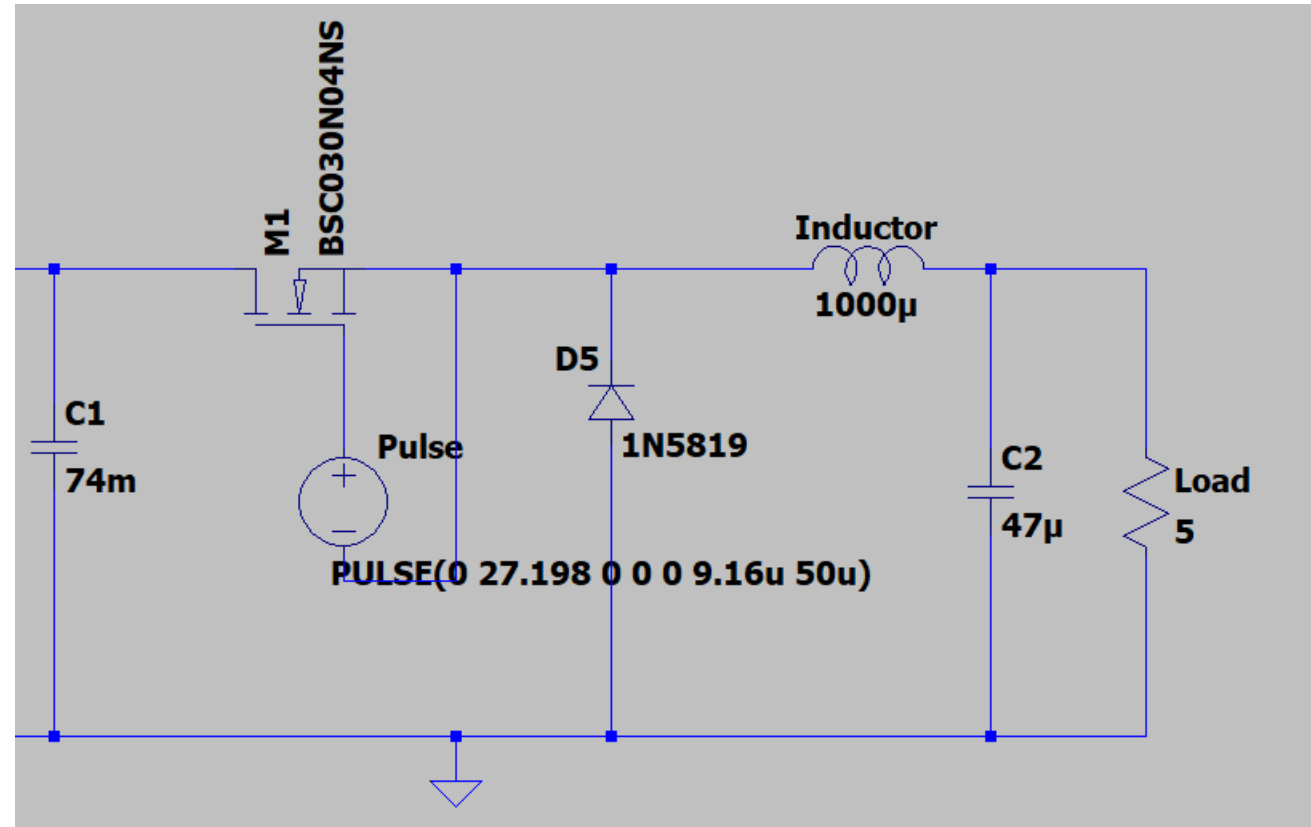
2.3 Buck converter stage

- Mosfet BSC030N04NS is use as a switch driven by pulse generator for that we need Ton time which can be calculated with Duty ratio



⇒ Nominal Duty ratio:-

$$D = \frac{V_{out}}{V_{in}} = \frac{5V}{27.28V}$$
$$D = 0.1832$$
$$\therefore T_{on} = \frac{D}{f_{sw}} = \frac{9.16 \times 10^{-3}}{10^3} = 9.16 \mu s$$



Calculations of Inductor and Output capacitor

⇒ calculation of Inductance and capacitor under nominal conditions:-

$$\Delta I_L = \frac{-(V_{out} - V_{in}) t_{on}}{L} = \frac{(V_{in} - V_{out}) \cdot D \cdot T_s}{L}$$

$$\therefore L = \frac{(27.28V - 5V) \cdot 0.1832 \times 1}{0.25 \cdot 20 \times 10^3 \text{ Hz}}$$

$$\boxed{\therefore L = 816 \mu\text{H}}$$

$$\therefore \Delta V_{C_{pp}} = \frac{\Delta I_L}{8 f_{sw} C} \Rightarrow C = \frac{\Delta I_L}{\Delta V_{C_{pp}} \times 8 \times f_{sw}}$$

$$C = \frac{0.25}{0.015 \times 5 \times 8 \times 20 \times 10^3 \text{ Hz}} = 20.8 \mu\text{F}$$

Considering System constraints

⇒ Now considering system constraints!

- Input voltage variations of $\pm 20\%$.
- switching frequency variation of $\pm 20\%$.

| V_{in} | f_{sw} | Inductor | capacitor | Worst case |
|----------|----------|----------------|------------|------------|
| +20% | +20% | 708,5 μH | 25 μF | |
| | -20% | 1062,7 μH | 37 μF | |
| -20% | +20% | 641 μH | 25 μF | |
| | -20% | 942 μH | 37 μF | |

Closest real components will be :-

Inductor :-

1000 μH

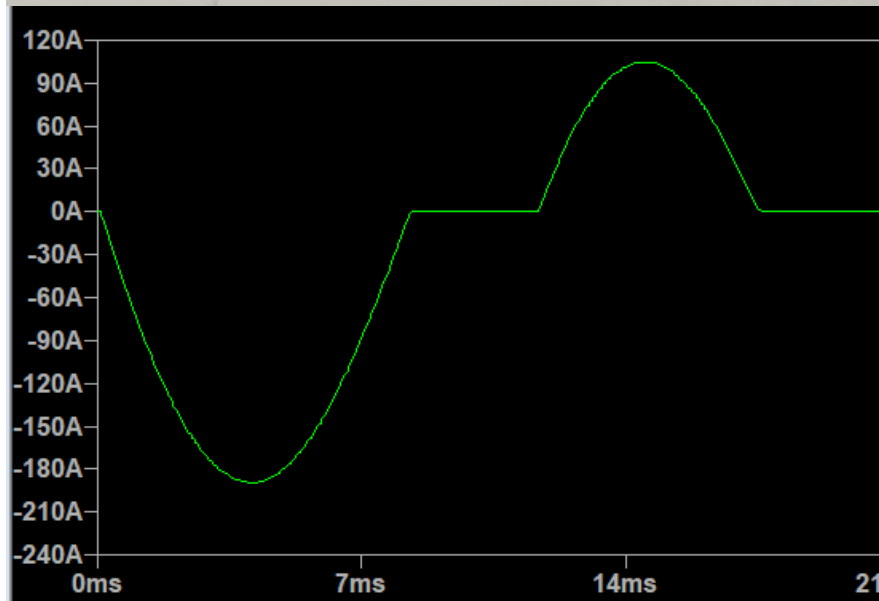
Capacitor :-

47 μF

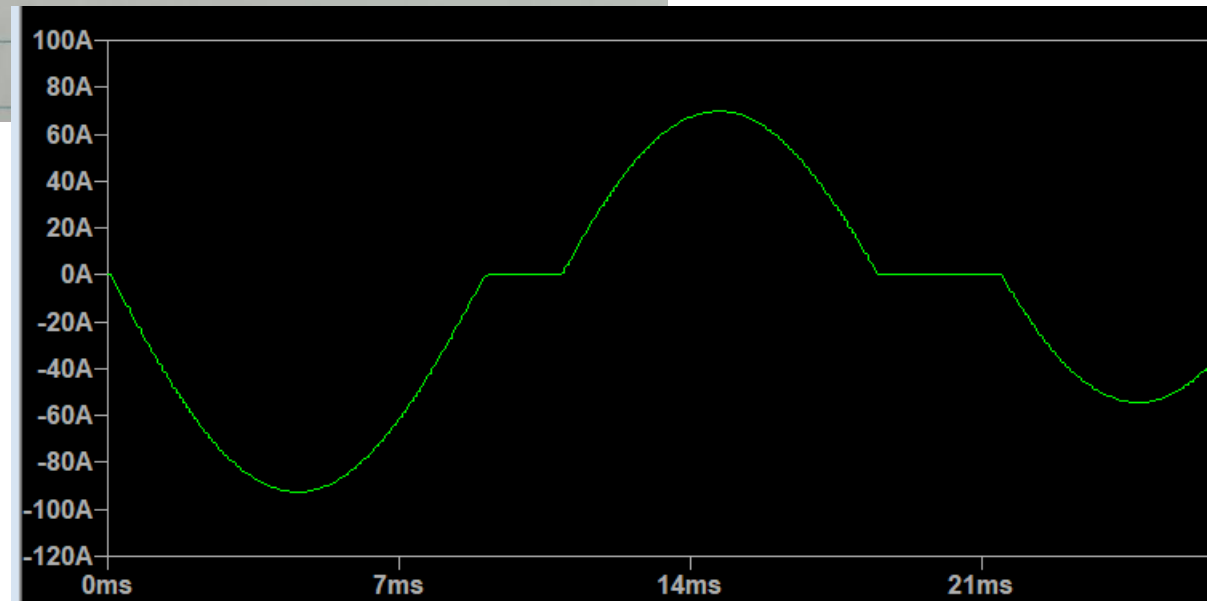
Surge current resistor

⇒ Surge resistor:-

$$I = 189 \text{ A}, V = 20\sqrt{2}$$
$$V = IR$$
$$\therefore R = \frac{20\sqrt{2} \text{ V}}{189 \text{ A}} = 0.149 \Omega \approx 0.15 \Omega$$

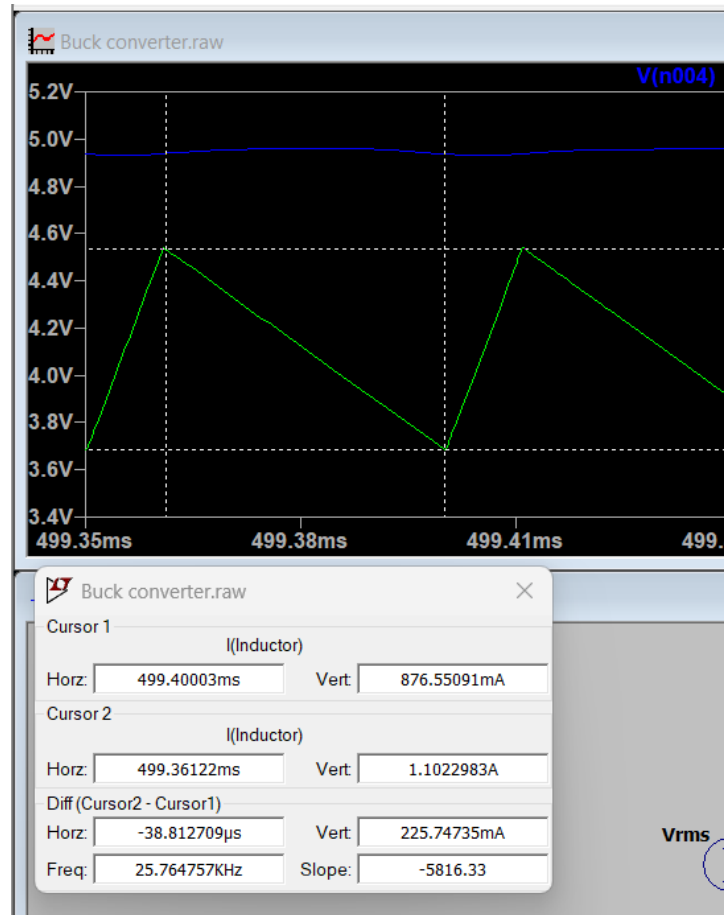


Initial current through capacitor w/o surge resistor

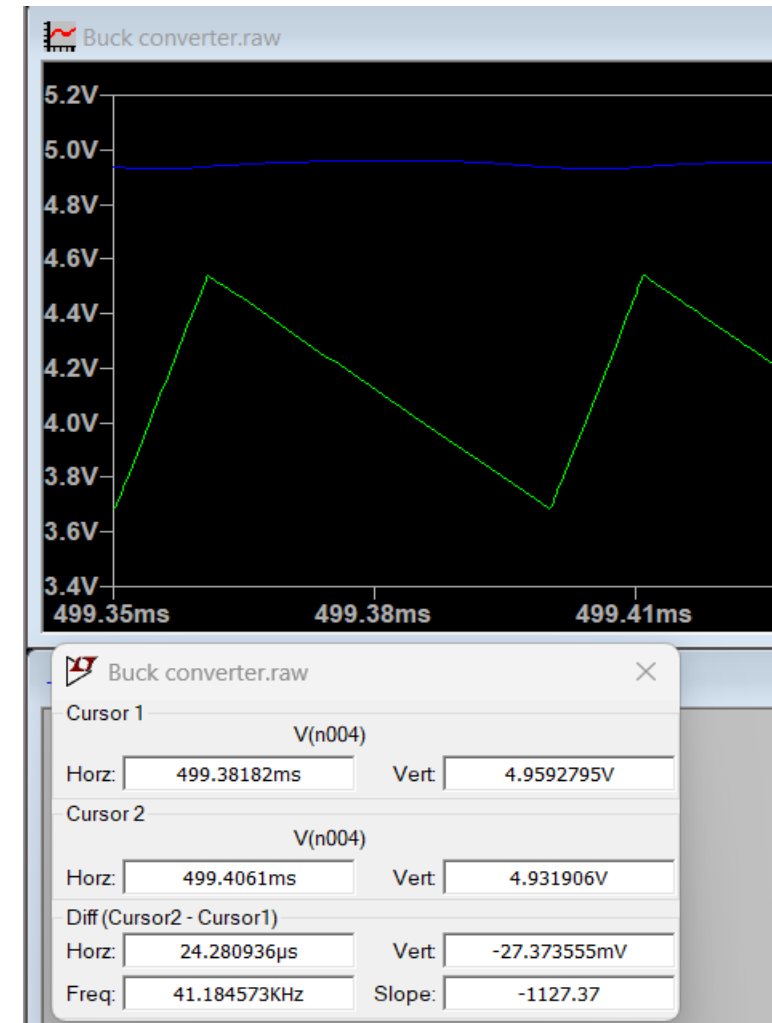


With surge resistor

Output ripple



Current ripple = 22.5%



Voltage ripple = 2.5%

*can be reduced by reducing resistance through inductor

Real Components with data sheets

BSC030N04NS G



MOSFET

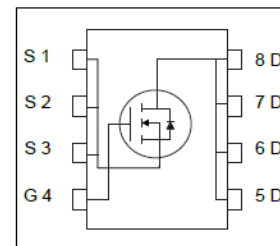
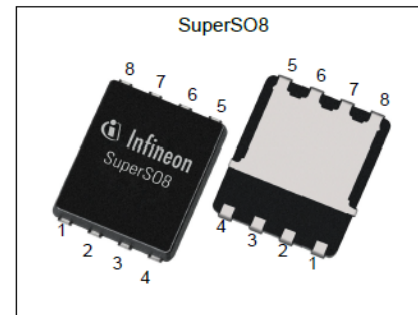
OptiMOS™3 Power-Transistor, 40 V

Features

- Fast switching MOSFET for SMPS
- Optimized technology for DC/DC converters
- Qualified according to JEDEC¹⁾ for target applications
- N-channel; Normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- Superior thermal resistance
- 100% Avalanche tested
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Table 1 Key Performance Parameters

| Parameter | Value | Unit |
|------------------|-------|------------|
| V_{DS} | 40 | V |
| $R_{DS(on),max}$ | 3.0 | m Ω |
| I_D | 132 | A |



Justification

- As our circuit operates with an input voltage of 22v to 33v, we need MOSFET with $V_{ds} > 33v$ with $I_d > 1amp$

Shielded Power Inductors MSS1812T



- 7 inductance values from 100 μ H to 1000 μ H
- Very low DCR and excellent current handling
- AEC-Q200 Grade 1 (-40°C to $+125^{\circ}\text{C}$)
- Designer's Kit C499 contains 3 of each part

Core material Ferrite

Core and winding loss See www.coilcraft.com/coreloss

Environmental RoHS compliant, halogen free

Terminations RoHS compliant matte tin over nickel over phos bronze. Other terminations available at additional cost.

Weight: 11.82 – 13.26 g

Operating voltage 400 V max

Ambient temperature -40°C to $+125^{\circ}\text{C}$ with (40°C rise) Irms current.

Maximum part temperature $+165^{\circ}\text{C}$ (ambient + temp rise). [Derating](#).

Storage temperature Component: -40°C to $+165^{\circ}\text{C}$.

Tape and reel packaging: -40°C to $+80^{\circ}\text{C}$

Resistance to soldering heat Max three 40 second reflows at $+260^{\circ}\text{C}$, parts cooled to room temperature between cycles

Moisture Sensitivity Level (MSL) 1 (unlimited floor life at $<30^{\circ}\text{C}$ / 85% relative humidity)

PCB washing Tested to MIL-STD-202 Method 215 plus an additional aqueous wash. See [Doc787_PCB_Washing.pdf](#).

| Part number ¹ | Inductance ² (μ H) | DCR (Ohms) ³ | | SRF typ ⁴ (MHz) | Isat (A) ⁵ | | | Irms (A) ⁶ | |
|--------------------------|---------------------------------------|-------------------------|-------|----------------------------------|-----------------------|-------------|-------------|-----------------------|--------------|
| | | typ | max | | 10% drop | 20% drop | 30% drop | 20°C rise | 40°C rise |
| MSS1812T-104MED | 100 $\pm 20\%$ | 0.045 | 0.052 | 3.3 | 5.2 | 5.8 | 6.0 | 2.87 | 4.35 |
| MSS1812T-154KED | 150 $\pm 10\%$ | 0.057 | 0.066 | 2.8 | 4.2 | 4.6 | 4.8 | 2.50 | 3.80 |
| MSS1812T-224KED | 220 $\pm 10\%$ | 0.086 | 0.098 | 2.3 | 3.6 | 3.8 | 4.0 | 2.09 | 3.16 |
| MSS1812T-334KED | 330 $\pm 10\%$ | 0.13 | 0.15 | 1.8 | 2.9 | 3.1 | 3.1 | 1.68 | 2.55 |
| MSS1812T-474KED | 470 $\pm 10\%$ | 0.20 | 0.23 | 1.35 | 2.4 | 2.7 | 2.8 | 1.39 | 2.10 |
| MSS1812T-684KED | 680 $\pm 10\%$ | 0.24 | 0.27 | 1.33 | 2.0 | 2.2 | 2.3 | 1.24 | 1.88 |
| MSS1812T-105KED | 1000 $\pm 10\%$ | 0.45 | 0.52 | 0.85 | 1.7 | 1.8 | 1.8 | 0.93 | 1.40 |

Inductor for worst case

Chip Monolithic Ceramic Capacitor for General
GRM32ER61A476KE20_ (1210, X5R:EIA, 47uF, DC10V)
_: packaging code

Reference Sheet

1.Scope

This product specification is applied to Chip Monolithic Ceramic Capacitor used for General Electronic equipment.

2.MURATA Part NO. System

(Ex.)

GRM

32

E

R6

1A

476

K

E20

L

(1)L/W
Dimensions

(2)T
Dimensions

(3)Temperature
Characteristics

(4)Rated
Voltage

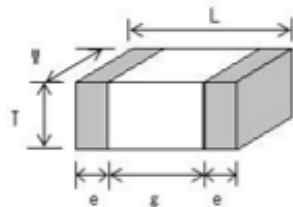
(5)Nominal
Capacitance

(6)Capacitance
Tolerance

(7)Murata's Control
Code

(8)Packaging Code

3. Type & Dimensions



(Unit:mm)

| | | | | |
|---------|---------|---------|----------|----------|
| (1)-1 L | (1)-2 W | (2) T | e | g |
| 3.2±0.3 | 2.5±0.2 | 2.5±0.2 | 0.3 min. | 1.0 min. |

4.Rated value

| (3) Temperature Characteristics (Public STD Code):X5R(EIA) | | (4) Rated Voltage | (5) Nominal Capacitance | (6) Capacitance Tolerance | Specifications and Test Methods (Operating Temp. Range) |
|---|----------------------------|-------------------------|----------------------------|---------------------------------|--|
| Temp. coeff or Cap. Change | Temp. Range (Ref.Temp.) | | | | |
| -15 to 15 % | -55 to 85 °C (25 °C) | DC 10 V | 47 uF | ±10 % | -55 to 85 °C |

Thanks for your attention